

### **Description**

The SSM3K335R,LF uses advanced trench technology

to provide excellent  $R_{\text{DS}(\text{ON})}$ , low gate charge and

operation with gate voltages as low as 2.5V. This

device is suitable for use as a

Battery protection or in other Switching application.

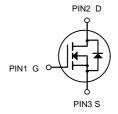


**SOT-23** 

#### **General Features**

 $V_{DS} = 30V I_{D} = 5.8A$ 

 $R_{DS(ON)} < 30 m\Omega$  @  $V_{GS}=10V$ 



N-Channel MOSFET

## **Application**

Battery protection

Load switch

Uninterruptible power supply

#### **Package Marking and Ordering Information**

Product ID	Pack	Marking	Qty(PCS)
SSM3K335R,LF	SOT-23	A09T XXXX	3000

## Absolute Maximum Ratings (T<sub>A</sub>=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
VDS	Drain-Source Voltage	30	V
Vgs	Gate-Source Voltage	±12	V
I <sub>D</sub>	Drain Current-Continuous	5.8	А
Ірм	Drain Current-Pulsed (Note 1)	30	А
P <sub>D</sub>	Maximum Power Dissipation	1.4	W
TJ,TstG	Operating Junction and Storage Temperature Range	-55 To 150	${\mathbb C}$
RөJA	Thermal Resistance,Junction-to-Ambient (Note 2)	89	СW



# Electrical Characteristics (T<sub>A</sub>=25 ℃ unless otherwise noted)

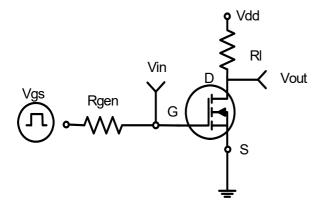
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	30	33	-	V
Zero Gate Voltage Drain Current	loss	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	Igss	V <sub>GS</sub> =±12V,V <sub>DS</sub> =0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	$V_{DS}=V_{GS},I_{D}=250\mu A$	0.7	0.9	1.4	V
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =4A	-	41	55	mΩ
Drain-Source On-State Resistance	RDS(ON)	V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A	-	32	42	mΩ
		V <sub>GS</sub> =10V, I <sub>D</sub> =5.8A	-	28	30	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =5A	10	-	-	S
Input Capacitance	Clss		-	825	-	PF
Output Capacitance	Coss	V <sub>DS</sub> =15V,V <sub>GS</sub> =0V,	-	100	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	78	-	PF
Turn-on Delay Time	t <sub>d(on)</sub>		-	3.3	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =15V, $R_L$ =2.7 $\Omega$	-	4.8	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10 $V$ , $R_{GEN}$ =3 $\Omega$	-	26	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	4	-	nS
Total Gate Charge	Qg		-	10	-	nC
Gate-Source Charge	Qgs	V <sub>DS</sub> =15V,I <sub>D</sub> =5.8A,	-	1.6	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =4.5V	-	3.1	-	nC
Diode Forward Voltage (Note 3)	VsD	V <sub>GS</sub> =0V,I <sub>S</sub> =5.8A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	5.8	Α

#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



# **Typical Electrical and Thermal Characteristics**



**Figure 1:Switching Test Circuit** 

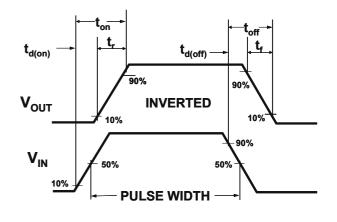


Figure 2:Switching Waveforms

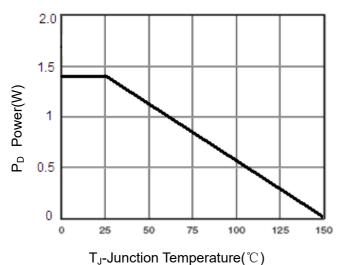
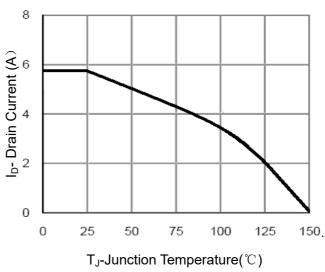
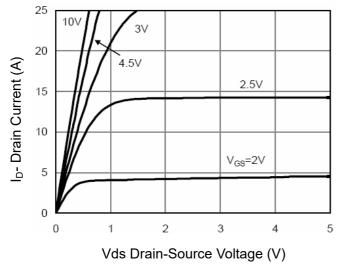


Figure 3 Power Dissipation



**Figure 4 Drain Current** 



**Figure 5 Output Characteristics** 

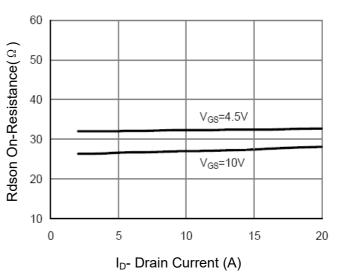
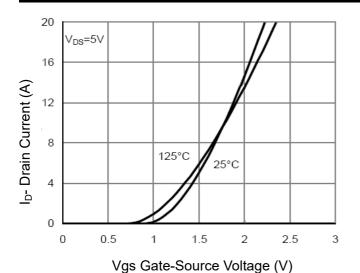
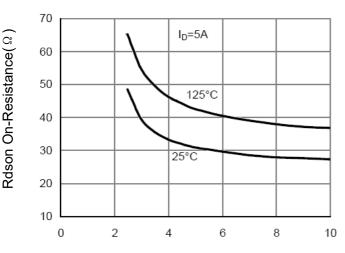


Figure 6 Drain-Source On-Resistance



**Figure 7 Transfer Characteristics** 



Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs

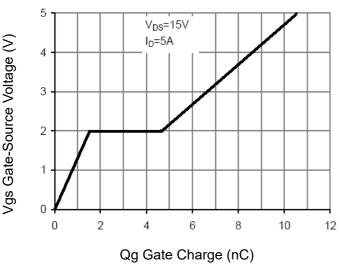


Figure 11 Gate Charge

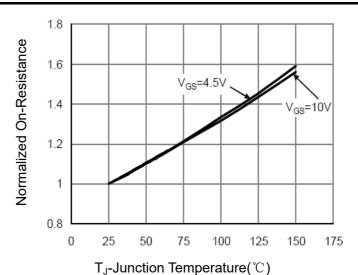


Figure 8 Drain-Source On-Resistance

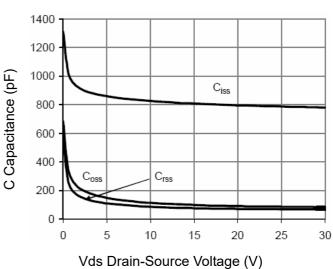


Figure 10 Capacitance vs Vds

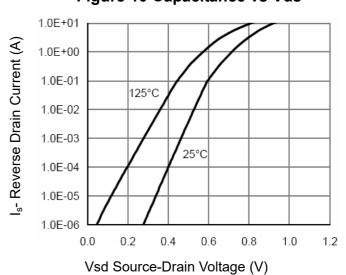
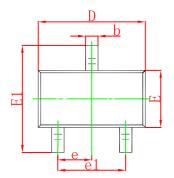
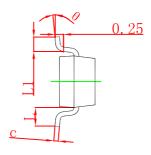


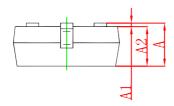
Figure 12 Source- Drain Diode Forward



# **SOT-23 Package Outline Dimensions**

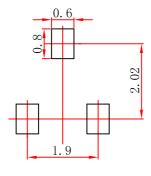






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	TYP	0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# **SOT-23 Suggested Pad Layout**



- Note:
  1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.



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